

**SCHOTTKY RECTIFIER**  
 HIGH EFFICIENCY SERIES

**35GQ150**  
 35 Amp, 150V

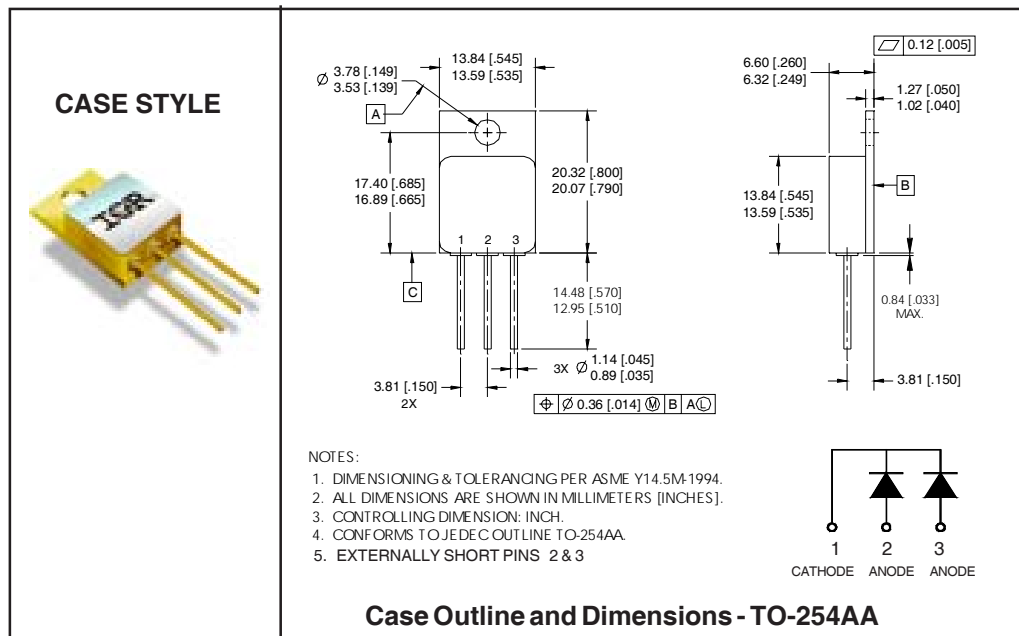
**Major Ratings and Characteristics**

Characteristics	35GQ150	Units
$I_{F(AV)}$	35	A
$V_{RRM}$	150	V
$I_{FSM}$ @ $t_p = 8.3ms$ half-sine	400	A
$V_F$ @ 35Apk, $T_J = 125^\circ C$	0.9	V
$T_J, T_{stg}$ Operating and storage	-55 to 150	$^\circ C$

**Description/Features**

The 35GQ150 Schottky rectifier has been expressly designed to meet the rigorous requirements of HiRel environments. It is packaged in the hermetically isolated TO-254AA package. The device's forward voltage drop and reverse leakage current are optimized for the lowest power loss and the highest circuit efficiency for typical high frequency switching power supplies and resonant power converters. Full MIL-PRF-19500 quality conformance testing is available on source control drawings to TX, TXV and S quality levels.

- Hermetically Sealed
- Low Forward Voltage Drop
- High Frequency Operation
- Guard Ring for Enhanced Ruggedness and Long term Reliability
- Lightweight
- ESD Rating: Class NS per MIL-STD-750, Method 1020



### Voltage Ratings

Part number	35GQ150
V <sub>R</sub> Max. DC Reverse Voltage (V)	150
V <sub>RWM</sub> Max. Working Peak Reverse Voltage (V)	

### Absolute Maximum Ratings

Parameters	Limits	Units	Conditions
I <sub>F(AV)</sub> Max. Average Forward Current See Fig. 5	35	A	50% duty cycle @ T <sub>C</sub> = 100 °C, square waveform
I <sub>FSM</sub> Max. Peak One Cycle Non - Repetitive Surge Current	400	A	@ t <sub>p</sub> = 8.3 ms half-sine

### Electrical Specifications

Parameters	Limits	Units	Conditions	
V <sub>FM</sub> Max. Forward Voltage Drop See Fig. 1 ①	1.12	V	@35A	T <sub>J</sub> = -55°C ②
	1.41	V	@70A	
	1.0	V	@35A	T <sub>J</sub> = 25°C ②
	1.31	V	@70A	
	0.9	V	@35A	T <sub>J</sub> = 125°C ②
	1.26	V	@70A	
I <sub>RM</sub> Max. Reverse Leakage Current See Fig. 2 ①	0.2	mA	T <sub>J</sub> = 25°C	V <sub>R</sub> = rated V <sub>R</sub> ②
	32	mA	T <sub>J</sub> = 125°C	
C <sub>T</sub> Max. Junction Capacitance	1600	pF	V <sub>R</sub> = 5V <sub>DC</sub> (1MHz, 25°C)	
L <sub>S</sub> Typical Series Inductance	7.8	nH	Measured from center of cathode pad to center of anode pad	

### Thermal-Mechanical Specifications

Parameters	Limits	Units	Conditions
T <sub>J</sub> Max. Junction Temperature Range	-55 to 150	°C	
T <sub>stg</sub> Max. Storage Temperature Range	-55 to 150	°C	
R <sub>thJC</sub> Max. Thermal Resistance, Junction to Case	1.1	°C/W	DC operation See Fig. 4
wt Weight (Typical)	9.3	g	
Die Size (Typical)	(2)158X158	mils	
Case Style	TO-254AA		

① Pulse Width < 300µs, Duty Cycle < 2%

② Pins 2 and 3 externally tied together

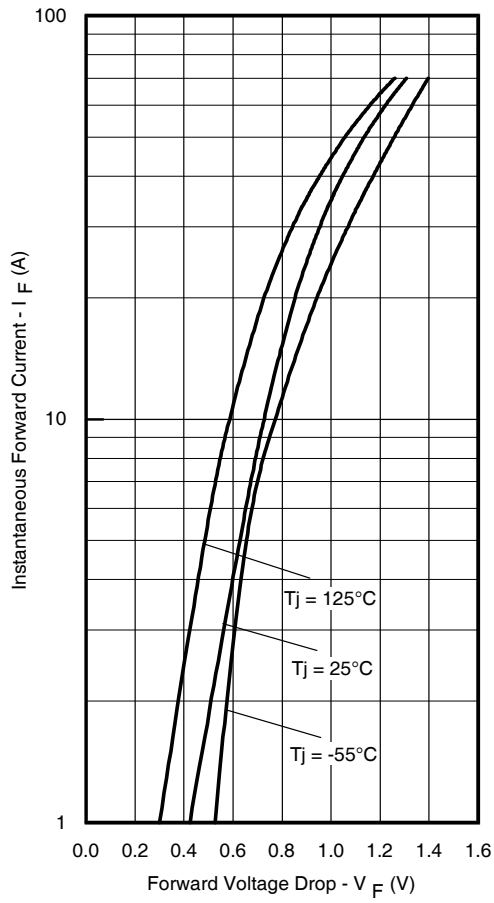


Fig. 1 - Max. Forward Voltage Drop Characteristics

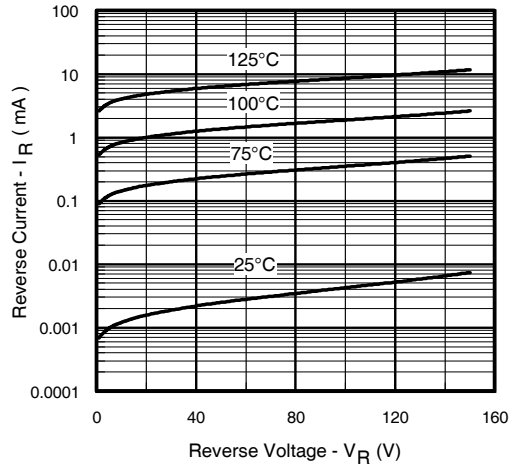


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

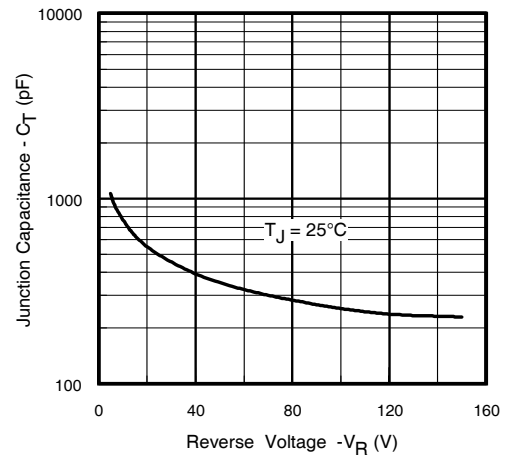


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

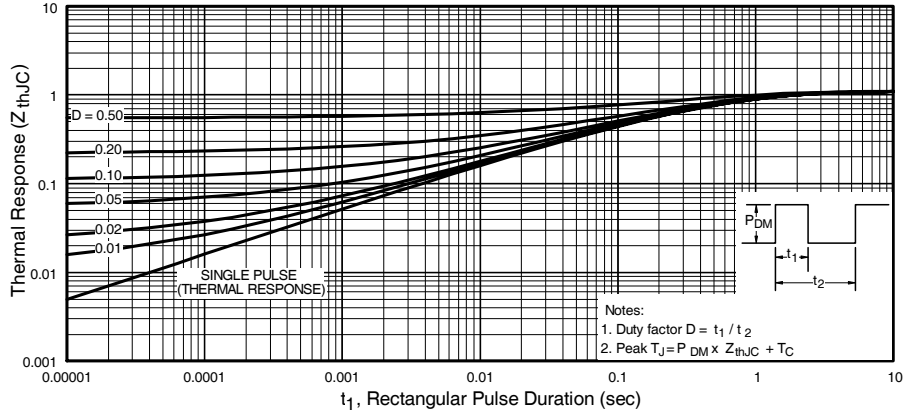


Fig. 4 - Max. Thermal Impedance  $Z_{thJC}$  Characteristics

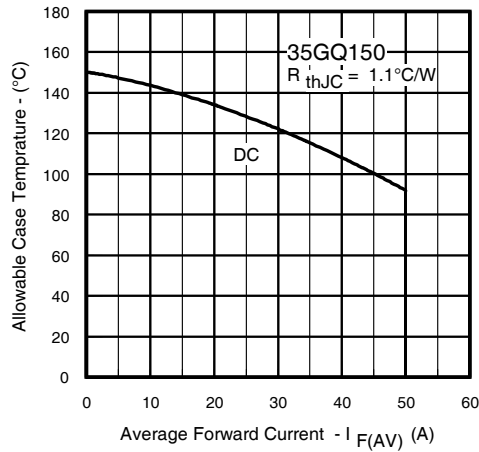


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current